TOSHIBA Transistor Silicon NPN Triple Diffused Type (PCT Process)

2SC2230,2SC2230A

High-Voltage General Amplifier Applications Color TV Class-B Sound Output Applications

- High breakdown voltage: $V_{CEO} = 180 \text{ V} (2SC2230A)$
- High DC current gain

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	200	V	
Collector-emitter voltage	2SC2230	V _{CEO}	160	V	
	2SC2230A	V CEO	180		
Emitter-base voltage		V _{EBO}	5	V	
Collector current		I _C	100	mA	
Base current		Ι _Β	50	mA	
Collector power dissipation		PC	800	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

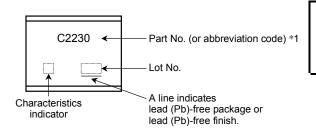
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

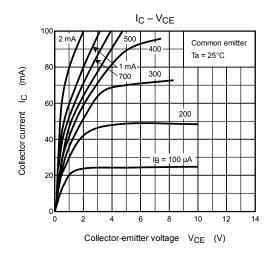
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 200 V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μA
DC current gain	h _{FE (1)} (Note)	V _{CE} = 10 V, I _C = 10 mA	120	_	400	
	h _{FE (2)}	V _{CE} = 10 V, I _C = 50 mA	80	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 50 mA, I _B = 5 mA	_	_	0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 10 V, I _C = 1 mA	0.50	0.60	0.70	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 10 mA	50	_	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	_	7.0	pF

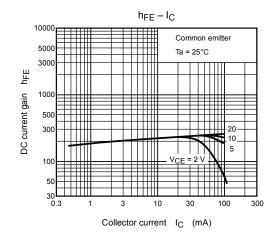
Note: hFE (1) classification Y: 120 to 240, GR: 200 to 400

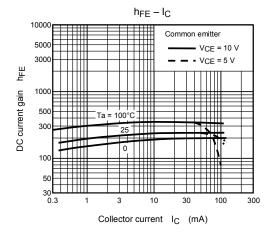
Marking

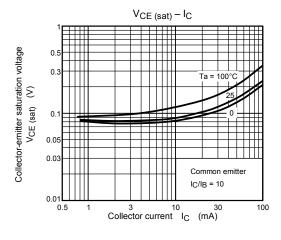


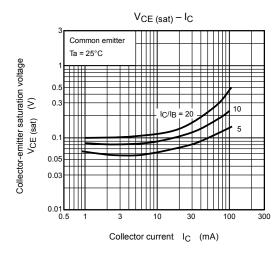
*1	Part No. (or abbreviation code)	Part No.		
	C2230	2SC2230		
	C2230A	2SC2230A		

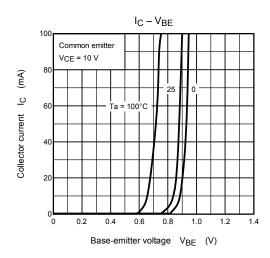


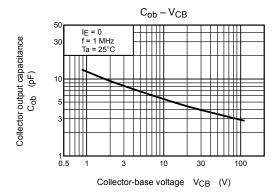


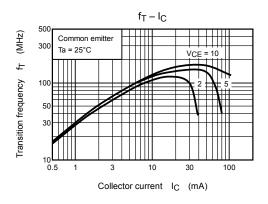


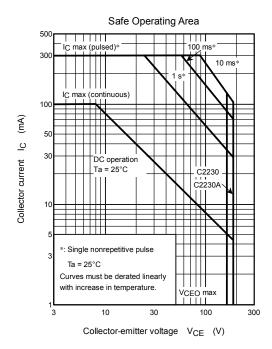












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